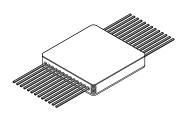
MIL-PRF-38534 AND 38535 CERTIFIED FACILITY

RAD HARD DUAL HIGH SIDE DRIVER WITH CURRENT SENSE 6000RH M.S.KENNEDY CORP.

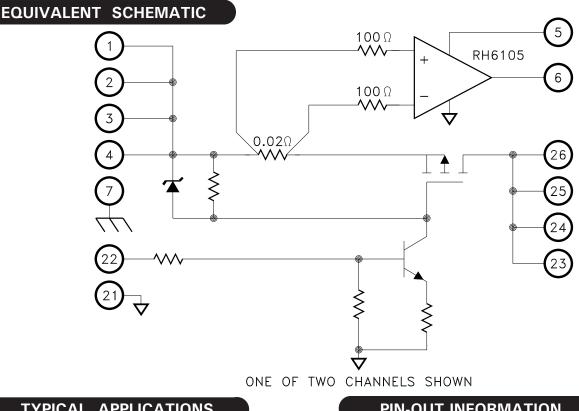
FEATURES:

- INEAD OGY RH 6105 Dice
- Radiation Hardened to 100Krad(Si) (Method 1019 Condition A)
- 100V RAD HARD MOSFETs
- Dual Configuration
- · Low Profile Surface Mount Flatpack
- 12V to 44V Input Voltage Range
- 5V to 36V VCC Supply Range
- 5A Max. Rating for Rad Hard Switches
- Contact MSK for MIL-PRF-38534 Qualification Status

DESCRIPTION:



The MSK6000RH is a radiation hardened dual 5A high side switch module with a current sensing output. Each switch is independently controlled with 5V logic and can switch up to 5A maximum current. Each switch has its own independent ground reference. The current monitor outputs provide a simple method for monitoring the current in each switch. The device is designed for space applications where quality, performance and low weight are a must. The MSK6000RH is packaged in a hermetic 26 pin flatpack.



TYPICAL APPLICATIONS

- · High Side Switch Drivers
- High Level Switching
- Space Applications
- Circuit Breaker

				AIIO	
1	VINA	18	VOUTB	26	VOUTA
2	VINA	17	VOUTB	25	VOUTA
3	VINA	16	VOUTB	24	VOUTA
4	VINA	15	CTLB	23	VOUTA
5	VCCA	14	GNDB	22	CTLA
6	IMONA	13	IMONB	21	GNDA
7	CASE	12	VCCB	20	CASE
8	VINB	11	VINB	19	VOUTB
9	VINB	10	VINB		
	- 3 4 5 6 7 8	 VINA VINA VINA VINA VINA VINA VCCA IMONA CASE VINB 	2 VINA 17 3 VINA 16 4 VINA 15 5 VCCA 14 6 IMONA 13 7 CASE 12 8 VINB 11	1VINA18VOUTB2VINA17VOUTB3VINA16VOUTB4VINA15CTLB5VCCA14GNDB6IMONA13IMONB7CASE12VCCB8VINB11VINB	1 VINA 18 VOUTB 26 2 VINA 17 VOUTB 25 3 VINA 16 VOUTB 24 4 VINA 15 CTLB 23 5 VCCA 14 GNDB 22 6 IMONA 13 IMONB 21 7 CASE 12 VCCB 20 8 VINB 11 VINB 19

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ABSOLUTE MAXIMUM RATINGS

VIN	Input Voltage	Ts
Vcc	Positive Supply Voltage	ΤL
TJ	Junction Temperature	
Vctl	Control Input Voltage	Тс
Ιουτ	Ouput Current	
Vout	Output Voltage	

4

Ts	Storage Temperature Range.		-55°C to +150°C
	eterage remperature nange.	• •	

ELECTRICAL SPECIFICATIONS

Parameter	Test Conditions (1)		Group A Subgroup	Min.	Тур.	Max.	Units
VCC Supply Current	Vctl=N/C		1,2,3	-	175	450	μA
VIN Conclus Concept	$V_{CTL} = N/C$ RL = N/C		1,2,3	-	30	125	μA
VIN Supply Current	Vctl = 4V RL = N/C		1,2,3	-	1.5	5.0	mA
Output Voltage (Off)	RL = 10K Ω		1,2,3	-	0.01	1.0	V
Switzelt On Designation	lout = 2.5A		1	-	0.26	0.40	Ω
Switch On Resistance (6)	VcTL = 4V		2,3	-	-	0.80	Ω
	Ιουτ = 2.5A	TON	4,5,6	-	4.2	10	uS
Output Delay Times	Measured @ 50% Points Of Input and Output	TOFF	4,5,6	-	21	40	uS
CTL Threshold	lout <u><</u> 100uA (OFF) lout <u><</u> 2.5A (ON)		1,2,3	0.8	2.4	4.0	v
CTL Input Current	VcTL=5V		1	-	-	850	uA
Output Current 2	Vctl=4V		1	5.0	-	-	A
	Iout = 2.5A		1	0.190	0.20	0.210	mA/A
IMON Gain		Post Irradiation	1	0.185	0.20	0.215	mA/A
Thermal Resistance	Junction to Case, Each MOSFET		-	-	5.0	5.5	°C/W

NOTES:

- (1) Unless otherwise specified the following test conditions shall apply: VCC = VIN = + 28V, IMON Resistor = $5K\Omega$ to ground. Parameter applies to each channel separately.
- 2) Parameter, if not tested shall be guaranteed to the specified limits in table 1.
- (2) Parameter, if not tested shall be guan (3) Subgroup 1,4 $TA = TC = +25 \,^{\circ}C$
 - Subgroup 2,5 $TA = TC = +125 \,^{\circ}C$
 - Subgroup 3,6 $TA = TC = -55 \,^{\circ}C$
- ④ Continuous operation at or above absolute maximum ratings may adversly effect the device performance and/or life cycle.
- (5) Pre and Post irradiation limits at 25°C, up to 100 Krad(Si) TID, are identical unless otherwise specified.
- 6 Includes internal sense resistor.

PIN FUNCTIONS

VIN - The VIN pins are connected to sources of MOSFETs. They provide the voltage supply that is switched to the output pins. High di/dt can be present at these pins during switch on and off transitions. Decoupling capacitors are recommended to minimize voltage spikes.

VCC - The VCC pins power the current sense amplifier. The VCC pins should be connected to low impedance positive supply source.

VOUT - The VOUT pins connect to drains of internal MOSFETs and are the device power outputs.

CTL - The CTL pins connect to the high side switch enabling circuits. When a logic high voltage is present, the high side switches turn on passing power from VIN to VOUT. The CTL pin threshold has no hysterisis. It operates in a linear region between 2.0V typical (OFF) and 2.7V typical (ON) at 25°C, 1.3V typical (OFF) and 2.2V typical (ON) at 125°C, and 2.6V typical (OFF) and 3.0V typical (ON) at -55°C. Input signals with fast transitions are recommended to prevent excessive power dissipation.

IMON - The IMON pins connect to the output of the internal RH6105 current sense amplifiers. Voltage drop across internal current sense resistor is amplified and a scaled current is sourced from the IMON pin. The ratio of IMON current to source current is 0.20mA/A. When terminated with a 5K Ω resistor the output voltage is 1V/A.

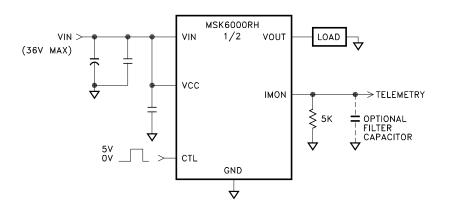
GND - The GND pins are the reference for each driver circuit. Each channel has it's own ground. The control input signals and current sense outputs are referenced to the respective grounds.

CASE - The CASE connection pins provide an electrical connection to the MSK6000RH package. They are electrically isolated from the internal circuitry.

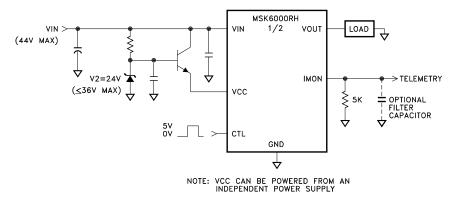
TOTAL DOSE RADIATION TEST PERFORMANCE

Radiation performance curves for TID testing have been generated for all radiation testing performed by MS Kennedy. These curves show performance trends throughout the TID test process and are located in the MSK6000RH radiation test report. The complete radiation test report is available in the RAD HARD PROD-UCTS section on the MSK website.

TYPICAL APPLICATION CIRCUIT



HIGH VIN APPLICATION CIRCUIT



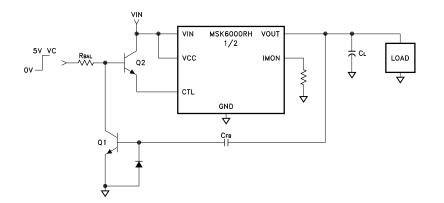
APPLICATION NOTES

VOUT RISE TIME CONTROL

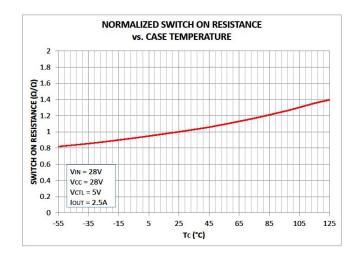
The output rise time of the MSK6000RH and the associated surge currents can be controlled over a wide range using a few external components as shown in the smplified schematic below. Power dissipation in the MSK6000RH can increase during turn on or bus voltage transients and should be considered. The circuit below performs the rise time control function by controlling the voltage drop V_R across R_{BAL}. Assuming a constant current to linearly change the output capacitance, the MSK6000RH rise time is approximated by the following equation:

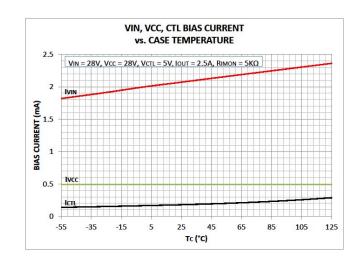
 $\frac{dV_{\text{OUT}}}{dt} = \frac{V_{\text{RBAL}}}{B_{\text{O1}} \ x \ R_{\text{BAL}} \ x \ C_{\text{FB}}} \text{ Where } V_{\text{RBAL}} = V_{\text{C}} - V_{\text{THRESHOLD}}$

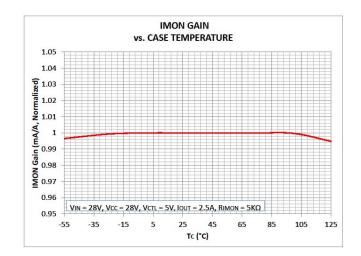
VOUT RISE TIME CONTROL CIRCUIT

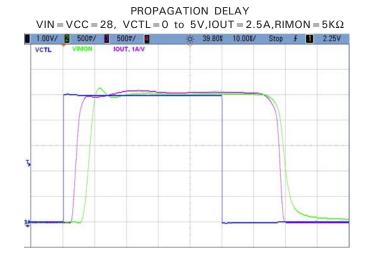


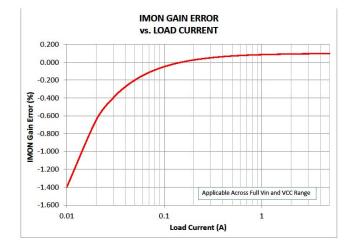
TYPICAL PERFORMANCE CURVES







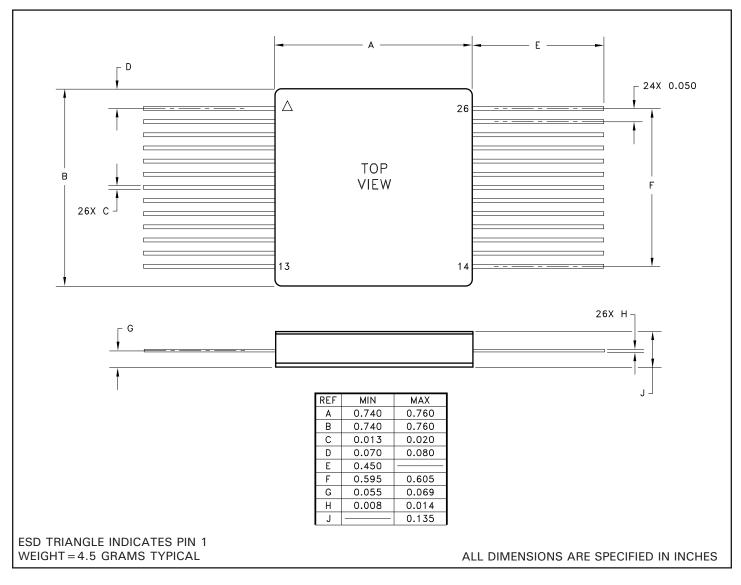




 $\label{eq:propagation delay} PROPAGATION DELAY \\ \mbox{VIN} = \mbox{VCC} = 28\mbox{V}, \mbox{VCTL} = 0 \mbox{ to } 5\mbox{V}, \mbox{IOUT} = 2.5\mbox{A}, \mbox{RIMON} = 5\mbox{K} \Omega \mbox{ II330pF} \\ \end{array}$



MECHANICAL SPECIFICATIONS



ORDERING INFORMATION

Part Number	Screening Level
MSK6000RH	Industrial
MSK6000HRH	MIL-PRF-38534 Class H
MSK6000KRH	MIL-PRF-38534 Class K

REVISION HISTORY

REV	STATUS	DATE	DESCRIPTION	
D	Released	05/14	Add high dose rate test bullet, add post rad specs and clarify dimensions.	
E	21116	06/14	dd ESD rating.	
F	21365	10/14	Add slew rate control app circuit, correct sheet 2 note 5.	

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